



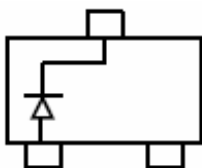
SOT-523 Plastic-Encapsulate Diodes

BAS21T SWITCHING DIODE

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

SOT-523



MARKING :T3

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Forward Continuous Current	I_{FM}	400	mA
Average Rectified Output Current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2.5 0.5	A
	@ t = 1.0μs @ t = 1.0s		
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	833	°C/W
Operating Junction Temperature	T_J	150	°C
Storage temperature	T_{STG}	-65-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	200		V
Reverse voltage leakage current	I_R	$V_R = 200V$		100	nA
Forward voltage	V_F	$I_F = 100mA$ $I_F = 200mA$		1 1.25	V
Total capacitance	C_T	$V_R = 0V, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 30mA, I_{rr} = 0.1I_R,$ $R_L = 100\Omega$		50	nS

Typical Characteristics

BAS21T

